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November 2013

FQPF7N60

N-Channel QFET $^{\mathbb{R}}$ MOSFET 600 V, 4.3 A, 1 Ω

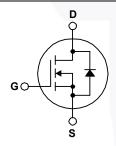
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 4.3 A, 600 V, $R_{DS}(on)$ = 1.0 Ω (Max.) @ V_{GS} = 10 V, I_{D} = 2.2 A
- · Low Gate Charge (Typ. 29 nC)
- Low C_{rss} (Typ. 16 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQPF7N60	Unit
V _{DSS}	Drain-Source Voltage		600	V
I _D	Drain Current - Continuous (T _C = 25°C)		4.3	Α
	- Continuous (T _C = 100°C))	2.7	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	17.2	А
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	580	mJ
I _{AR}	Avalanche Current	(Note 1)	4.3	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_{D}	Power Dissipation (T _C = 25°C)		48	W
	- Derate above 25°C		0.38	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQPF7N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.60	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF7N60	FQPF7N60	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Parameter	Test Conditions	Min	Тур	Max	Unit
aracteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.67		V/°C
Zoro Gato Voltago Prain Current	V _{DS} = 600 V, V _{GS} = 0 V			10	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 480 V, T _C = 125°C			100	μΑ
Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
•	Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward	tracteristics Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ μA}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$, Referenced to 25°C Zero Gate Voltage Drain Current $V_{DS} = 600 \text{ V}$, $V_{GS} = 0 \text{ V}$ $V_{DS} = 480 \text{ V}$, $V_{CS} = 125°C$ Gate-Body Leakage Current, Forward $V_{GS} = 30 \text{ V}$, $V_{DS} = 0 \text{ V}$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 2.2 \text{ A}$		0.8	1.0	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_{D} = 2.2 \text{ A}$		6.4		S

Dynamic Characteristics

C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	 1100	1430	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	 135	175	pF
C _{rss}	Reverse Transfer Capacitance		 16	21	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 7.4 A,		30	70	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		80	170	ns
t _{d(off)}	Turn-Off Delay Time			65	140	ns
t _f	Turn-Off Fall Time	(Note	4)	60	130	ns
Q_g	Total Gate Charge	V _{DS} = 480 V, I _D = 7.4 A,	-	29	38	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	A	7		nC
Q _{gd}	Gate-Drain Charge	(Note	4)	14.5	/	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		 	4.3	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		 	17.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 4.3 \text{ A}$	 	1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, I}_{S} = 7.4 \text{ A,}$	 320		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	 2.4		μС

- Notes: Notes: Notes: A Repetitive Rating: Pulse width limited by maximum junction temperature. 2. L = 57.6 mH, I_{AS} = 4.3 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} ≤ 7.4 A, di/dt ≤ 200 A/µs, V_{DD} ≤ B V_{DSS} , starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

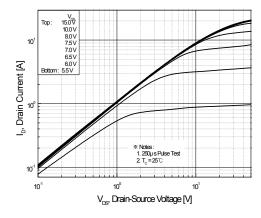


Figure 1. On-Region Characteristics

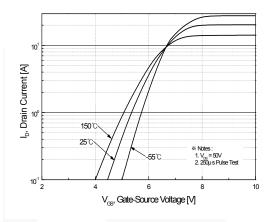


Figure 2. Transfer Characteristics

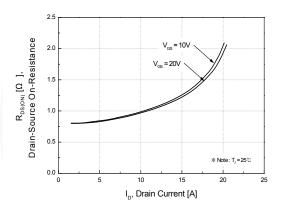


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

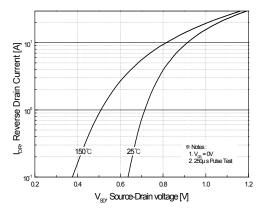


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

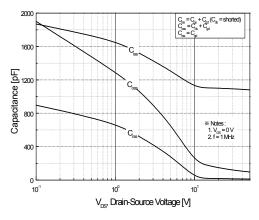


Figure 5. Capacitance Characteristics

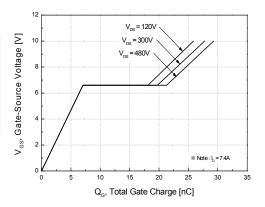


Figure 6. Gate Charge Characteristics

Typical Characteristics

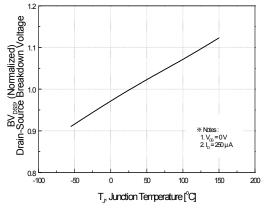
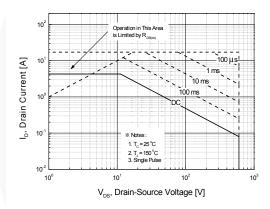


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



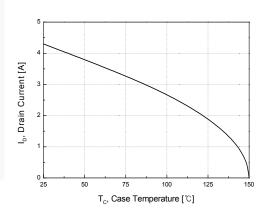


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

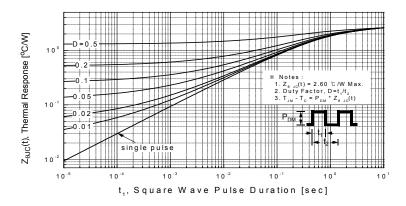


Figure 11. Transient Thermal Response Curve



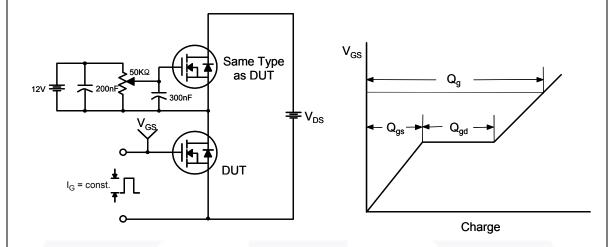


Figure 13. Resistive Switching Test Circuit & Waveforms

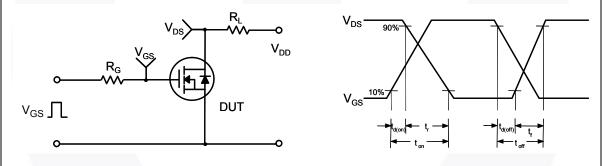
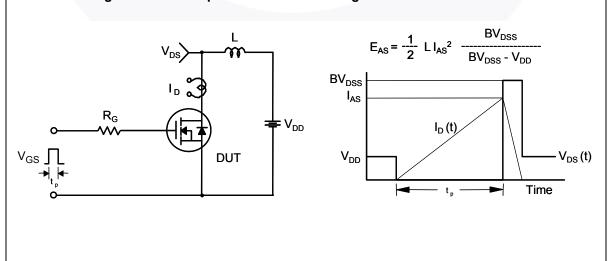
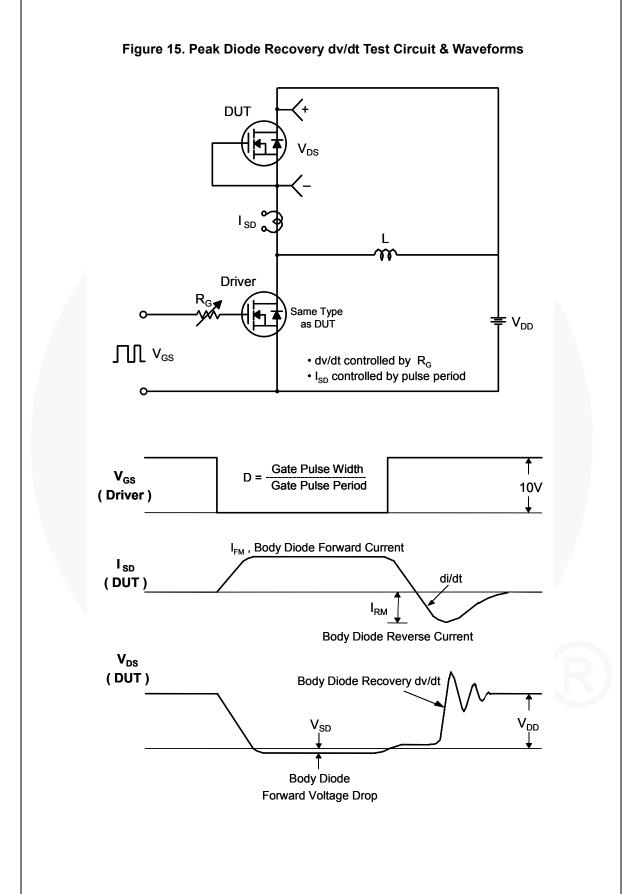


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





Mechanical Dimensions

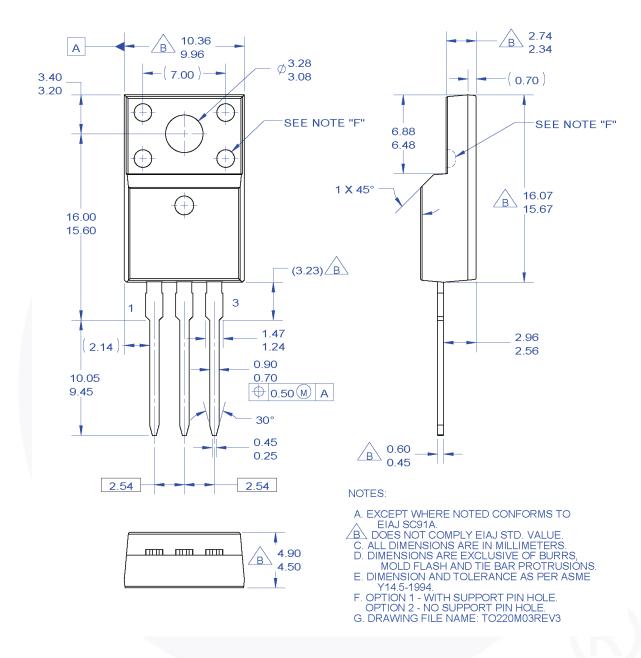


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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